



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>

## NTE458 N-Channel Silicon JFET General Purpose, Low Noise, Audio Frequency Amplifier TO92 Type package

**Features:**

- Very Low Noise
- Low Gate Current

**Absolute Maximum Ratings:** ( $T_A = +25^{\circ}\text{C}$  unless otherwise specified)

Gate-Drain Voltage, $V_{GDO}$ .....	-50V
Gate-Source Voltage, $V_{GSO}$ .....	-50V
Drain-Source Voltage ( $V_{DS} = -2V$ ), $V_{DSX}$ .....	50V
Drain Current, $I_D$ .....	20mA
Gate Current, $I_G$ .....	10mA
Total Device Dissipation, $P_T$ .....	250mW
Operating Junction Temperature, $T_J$ .....	+125 $^{\circ}\text{C}$
Storage Temperature Range, $T_{stg}$ .....	-55 $^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$

**Electrical Characteristics:** ( $T_A = +25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate Reverse Current	$I_{GSS}$	$V_{GS} = -20V, V_{DS} = 0$	-	-	-1	nA
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 10V, V_{GS} = 0$	0.5	3.0	12	mA
Gate-Source Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 10\mu A$	-0.13	-0.5	-1.5	V
Forward Transconductance	$g_{fs}$	$V_{DS} = 10V, I_D = 0.5mA, f = 1kHz$	4.0	5.2	-	mhos
		$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	4.0	12	-	mhos
Input Capacitance	$C_{iss}$	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	-	13	-	pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	-	2.6	-	pF
Noise Frequency	NF	$V_{DS} = 10V, V_{GS} = 0, R_G = 1k\Omega, f = 10Hz$	-	5.0	10	dB
		$V_{DS} = 10V, V_{GS} = 0, R_G = 1k\Omega, f = 100Hz$	-	1.0	3.0	dB
		$V_{DS} = 10V, V_{GS} = 0, R_G = 1k\Omega, f = 1kHz$	-	0.6	1.5	dB
Noise Voltage	NV	$I_D = 0.5mA, R_G = 1k\Omega, f = 10Hz \text{ to } 1kHz \text{ (at } V_G = -3dB)$	-	15	20	mV

